# **NPN Switching Transistor**

The MMBT4401M3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose switching applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	265 2.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	640 5.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

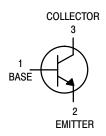
1

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



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### MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



AF M = Specific Device Code

M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT4401M3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit	
OFF CHARACTERISTICS		1	<u> </u>			
Collector - Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	-	Vdc		
Collector - Base Breakdown Voltage	$(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V <sub>(BR)CBO</sub>	60	-	Vdc	
Emitter - Base Breakdown Voltage	$(I_E = 0.1 \text{ mAdc}, I_C = 0)$	V <sub>(BR)EBO</sub>	6.0	-	Vdc	
Base Cutoff Current	(V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>BEV</sub>	-	0.1	μAdc	
Collector Cutoff Current	(V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>CEX</sub>	-	0.1	μAdc	
ON CHARACTERISTICS (Note 3)		1		1	1	
DC Current Gain	$ \begin{aligned} &(I_C = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ &(I_C = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ &(I_C = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ &(I_C = 150 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ &(I_C = 500 \text{ mAdc, V}_{CE} = 2.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	20 40 80 100 40	- - - 300 -	-	
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	- -	0.4 0.75	Vdc		
Base - Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.75 -	0.95 1.2	Vdc		
SMALL-SIGNAL CHARACTERISTIC	CS					
Current - Gain - Bandwidth Product	$(I_C = 20 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz})$	f <sub>T</sub>	250	-	MHz	
Collector-Base Capacitance	$(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C <sub>cb</sub>	_	6.5	pF	
Emitter-Base Capacitance	$(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C <sub>eb</sub>	_	30	pF	
Input Impedance ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )		h <sub>ie</sub>	1.0	15	kΩ	
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>re</sub>	0.1	8.0	X 10 <sup>-4</sup>	
Small – Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>fe</sub>	40	500	_	
tput Admittance ( $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$ )		h <sub>oe</sub>	1.0	30	μmhos	
SWITCHING CHARACTERISTICS						
Delay Time (V <sub>CC</sub> = 30 Vdc, V <sub>FB</sub> = 2.0 Vdc,		t <sub>d</sub>	-	15	P.0	
Rise Time	I <sub>C</sub> = 150 mAdc, I <sub>B1</sub> = 15 mAdc)	t <sub>r</sub>	-	20	ns	
Storage Time	orage Time $(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$		-	225		
Fall Time $I_{B1} = I_{B2} = 15 \text{ mAdc}$		t <sub>f</sub>	-	30	ns	

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

### **SWITCHING TIME EQUIVALENT TEST CIRCUITS**

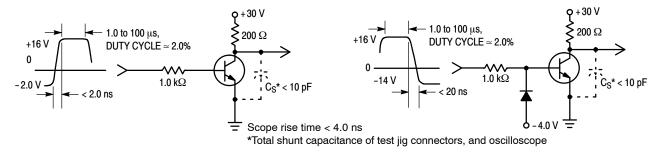


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

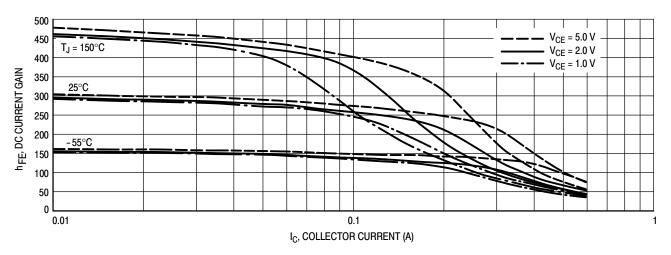


Figure 3. DC Current Gain

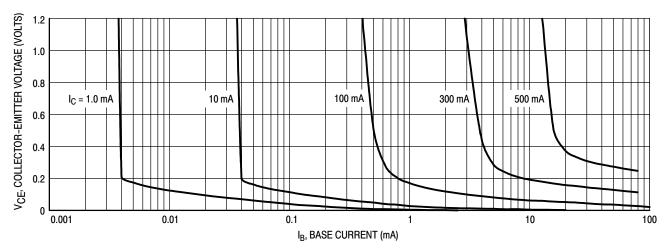


Figure 4. Collector Saturation Region

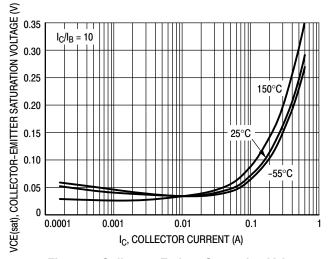


Figure 5. Collector-Emitter Saturation Voltage vs. Collector Current

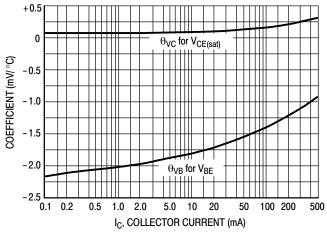


Figure 6. Temperature Coefficients

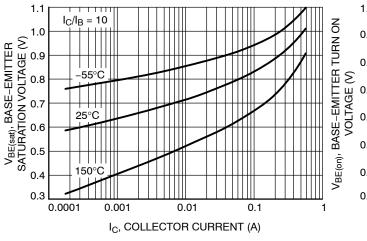


Figure 7. Base-Emitter Saturation Voltage vs. Collector Current

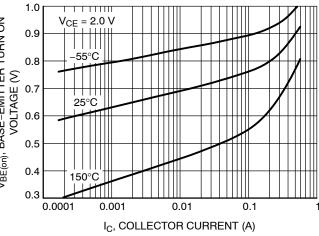


Figure 8. Base–Emitter Turn On Voltage vs.
Collector Current

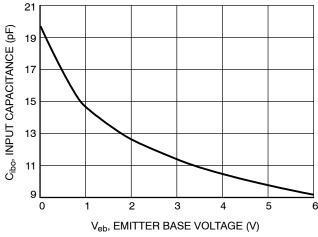


Figure 9. Input Capacitance vs. Emitter Base Voltage

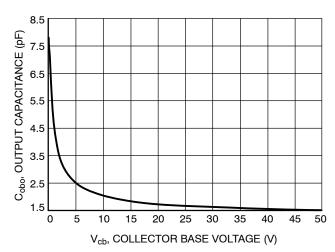
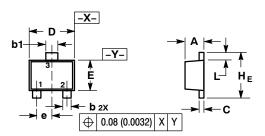


Figure 10. Output Capacitance vs. Collector Base Voltage

### PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE C



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

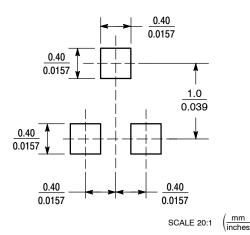
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS.

	MI	MILLIMETERS INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
С	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
е	0.40 BSC			0.016 BSC		
ΗE	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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